

# ADJUSTABLE BATTERY-BACKUP SUPERVISOR FOR RAM RETENTION

#### **FEATURES**

- Supply Current of 40 μA (Max)
- Battery Supply Current of 100 nA (Max)
- Supply Voltage Supervision Range:
  - Adjustable
  - Other Versions Available on Request
- Backup-Battery Voltage Can Exceed V<sub>DD</sub>
- Power-On Reset Generator With Fixed 100-ms Reset Delay Time
- Active-High and Active-Low Reset Output
- Chip-Enable Gating: 3 ns (at V<sub>DD</sub> = 5 V) Max Propagation Delay
- 10-Pin MSOP Package
- Temperature Range: -40°C to 85°C

#### **APPLICATIONS**

- Fax Machines
- Set-Top Boxes
- Advanced Voice Mail Systems
- Portable Battery-Powered Equipment
- Computer Equipment
- Advanced Modems
- Automotive Systems
- Portable Long-Time Monitoring Equipment
- Point-of-Sale Equipment

#### DESCRIPTION

The TPS3613-01 supervisory circuit monitors and controls processor activity by providing backup-battery switchover for data retention of CMOS RAM.

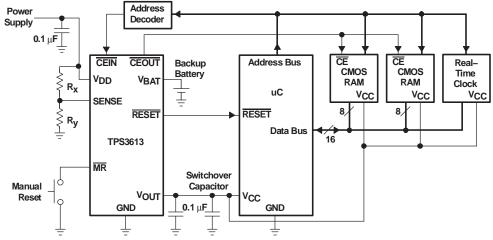
During power-on, reset (RESET and  $\overline{RESET}$ ) is asserted when the supply voltage (V<sub>DD</sub> or V<sub>BAT</sub>) becomes higher than 1.1 V.

Thereafter, the supply voltage supervisor monitors  $V_{DD}$  at the SENSE pin through external feedback resistors and keeps reset active as long as SENSE remains below the threshold voltage,  $V_{\text{IT}}$ .

An internal timer delays the release of the reset state to ensure proper system reset. The delay time starts after SENSE rises above the threshold voltage, V<sub>IT</sub>.

When SENSE drops below  $V_{\text{IT}}$ , reset becomes active again.

The TPS3613-01 is available in a 10-pin MSOP package and is characterized for operation over a temperature range of -40°C to +85°C.



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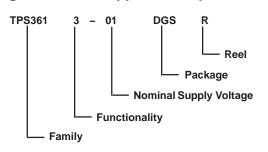


#### **PACKAGE INFORMATION**

T <sub>A</sub> DEVICE NAME		MARKING
-40°C to +85°C	TPS3613-01DGSR <sup>†</sup>	AFK

<sup>†</sup>The DGSR passive indicates tape and reel of 2500 parts.

## ordering information application specific versions



DEVICE NAME	NOMINAL VOLTAGE <sup>‡</sup> , V <sub>NOM</sub>
TPS3613-01 DGS	Adjustable

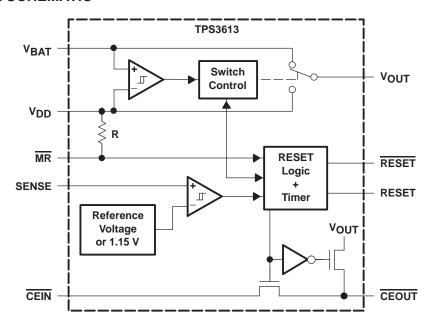
<sup>‡</sup> For other threshold voltages, contact the local TI sales office for availability and lead-time.

#### FUNCTION TABLE

FUNCTION TABLE									
SENSE > VIT	$V_{DD} > V_{BAT}$	MR	CEIN	V <sub>OUT</sub>	RESET	RESET	CEOUT		
0	0	0	0	VBAT	0	1	DIS		
0	0	0	1	VBAT	0	1	DIS		
0	0	1	0	V <sub>BAT</sub>	0	1	DIS		
0	0	1	1	VBAT	0	1	DIS		
0	1	0	0	$V_{DD}$	0	1	DIS		
0	1	0	1	$V_{DD}$	0	1	DIS		
0	1	1	0	$V_{DD}$	0	1	DIS		
0	1	1	1	$V_{DD}$	0	1	DIS		
1	0	0	0	$V_{DD}$	0	1	DIS		
1	0	0	1	$V_{DD}$	0	1	DIS		
1	0	1	0	$V_{DD}$	1	0	0		
1	0	1	1	$V_{DD}$	1	0	1		
1	1	0	0	$V_{DD}$	0	1	DIS		
1	1	0	1	$V_{DD}$	0	1	DIS		
1	1	1	0	$V_{DD}$	1	0	0		
1	1	1	1	$V_{DD}$	1	0	1		



#### **FUNCTIONAL SCHEMATIC**

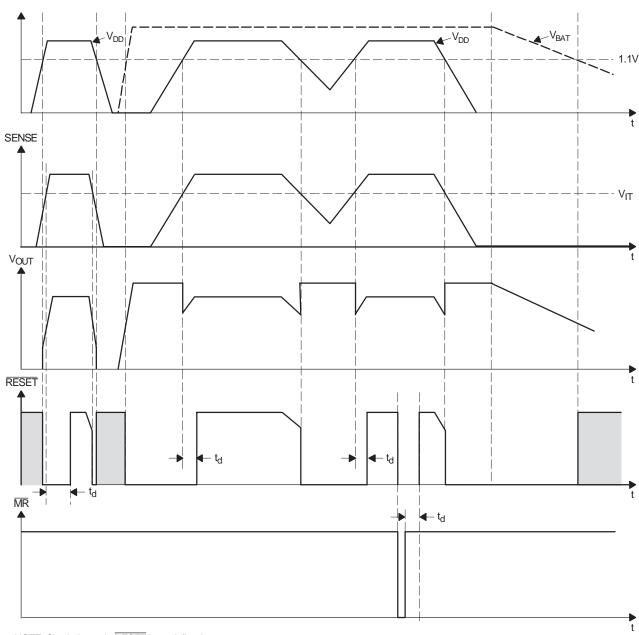


#### **Terminal Functions**

TERMIN	/INAL I/O		DESCRIPTION
NAME	NO.		
CEIN	5	I	Chip-enable input
CEOUT	6	0	Chip-enable output
GND	3	I	Ground
MR	4	I	Manual reset input
RESET	7	0	Active-high reset output
RESET	9	0	Active-low reset output
SENSE	8	I	Adjustable sense input, assumed to be connect to V <sub>DD</sub> throught feedback resistences. Call your local contacts for other application connections.
VBAT	10	I	Backup-battery input
$V_{DD}$	2	ı	Input supply voltage
VOUT	1	0	Supply output



#### **TIMING DIAGRAM**



NOTE: Shaded area in RESET is undefined.

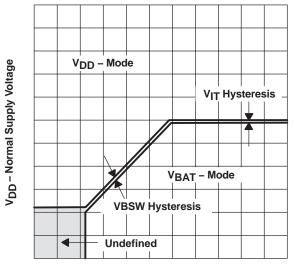


# detailed description backup-battery switchover

In case of a brownout or power failure, it may be necessary to preserve the contents of RAM. If a backup battery is installed at  $V_{BAT}$ , the device automatically switches the connected RAM to backup power when  $V_{DD}$  fails. In order to allow the backup battery (for example, 3.6-V lithium cells) to have a higher voltage than  $V_{DD}$ , these

supervisors do not connect V<sub>BAT</sub> to V<sub>OUT</sub> when V<sub>BAT</sub> is greater than V<sub>DD</sub>. V<sub>BAT</sub> only connects to V<sub>OUT</sub> (through a 15- $\Omega$  switch) when V<sub>DD</sub> falls below V<sub>IT</sub> and V<sub>BAT</sub> is greater than V<sub>DD</sub>. When V<sub>DD</sub> recovers, switchover is deferred either until V<sub>DD</sub> crosses V<sub>BAT</sub>, or when V<sub>DD</sub> rises above the reset threshold V<sub>IT</sub>. V<sub>OUT</sub> connects to V<sub>DD</sub> through a 1- $\Omega$  (max) PMOS switch when V<sub>DD</sub> crosses the reset threshold.

V <sub>DD</sub> >V <sub>BAT</sub>	V <sub>DD</sub> >V <sub>IT</sub>	Vout
1	1	$V_{DD}$
1	0	$V_{DD}$
0	1	$V_{DD}$
0	0	V <sub>BAT</sub>



VBAT - Backup-Battery Supply Voltage

Figure 1. V<sub>DD</sub> - V<sub>BAT</sub> Switchover



#### detailed description (continued)

#### chip-enable signal gating

The internal gating of chip-enable (\$\overline{CE}\$) signals prevents erroneous data from corrupting CMOS RAM during an under-voltage condition. The TPS3613 uses a series transmission gate from \$\overline{CEIN}\$ to \$\overline{CEOUT}\$. During normal operation (reset not asserted), the \$\overline{CE}\$ transmission gate is enabled and passes all \$\overline{CE}\$ transitions. When reset is asserted, this path becomes disabled, preventing erroneous data from corrupting the \$\overline{CMOS}\$ RAM. The short \$\overline{CE}\$ propagation delay from \$\overline{CEIN}\$ to \$\overline{CEOUT}\$ enables the \$\overline{CESCECUT}\$ enables to \$\overline{CESCECUT}\$ enables to \$\overline{CESCECUT}\$ enables to \$\overline{CESCECUT}\$ enables the \$\overline{CESCECUT}\$ device to be used with most processors.

The CE transmission gate is disabled and  $\overline{\text{CEIN}}$  is in high impedance (disable mode) while reset is asserted. During a power-down sequence when  $V_{DD}$  crosses the reset threshold, the  $\overline{\text{CEIN}}$  transmission gate is disabled and  $\overline{\text{CEIN}}$  immediately becomes high impedance if the voltage at  $\overline{\text{CEIN}}$  is high. If  $\overline{\text{CEIN}}$  is low when reset

is asserted, the CE transmission gate is disabled when  $\overline{\text{CEIN}}$  goes high, or 15  $\mu s$  after reset asserts, whichever occurs first. This allows the current write cycle to complete during power down. When the CE transmission gate is enabled, the impedance of  $\overline{\text{CEIN}}$  appears as a resistor in series with the load at  $\overline{\text{CEOUT}}$ . The overall device propagation delay through the CE transmission gate depends on  $V_{OUT}$ , the source impedance of the drive connected to  $\overline{\text{CEIN}}$ , and the load at  $\overline{\text{CEOUT}}$ . To achieve minimum propagation delay, the capacitive load at  $\overline{\text{CEOUT}}$  should be minimized, and a low-output-impedance driver is used.

In the disabled mode, the transmission gate is off and an active pullup connects  $\overline{\text{CEOUT}}$  to  $V_{OUT}$ . This pullup turns off when the transmission gate is enabled.

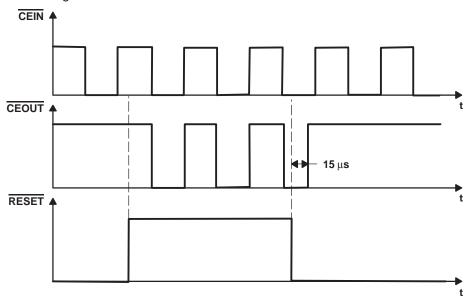


Figure 2. Chip-Enable Timing



# ABSOLUTE MAXIMUM RATINGS OVER OPERATING FREE-AIR TEMPERATURE (unless otherwise noted)(1)

Supply voltage: V <sub>DD</sub> <sup>(2)</sup>	7 V
MR and SENSE pins <sup>(2)</sup>	
Continuous output current at VOUT: IO	400 mA
All other pins, IO	±10 mA
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub>	–40°C to +85°C
Storage temperature range, T <sub>stq</sub>	65°C to +150°C
Lead temperature soldering 1,6 mm (1/16 inch) from case for 10 seconds .	+260°C
Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the o	device. These are stress ratings only, and

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le +25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = +25°C	T <sub>A</sub> = +70°C POWER RATING	T <sub>A</sub> = +85°C POWER RATING
DGS	424 mW	3.4 mW/°C	271 mW	220 mW

#### RECOMMENDED OPERATING CONDITIONS

	MIN	MAX	UNIT
Supply voltage, V <sub>DD</sub>	1.65	5.5	V
Battery supply voltage, V <sub>BAT</sub>	1.5	5.5	V
Input voltage, V <sub>I</sub>	0	V <sub>DD</sub> + 0.3	V
High-level input voltage, VIH	0.7 x V <sub>DD</sub>		V
Low-level input voltage, V <sub>IL</sub>		0.3 x V <sub>DD</sub>	V
Continuous output current at V <sub>OUT</sub> , I <sub>O</sub>		300	mA
Input transition rise and fall rate at $\overline{MR}$ , $\Delta t/\Delta V$		100	ns/V
Slew rate at V <sub>DD</sub> or V <sub>bat</sub>		1	V/μs
Operating free-air temperature range, TA	-40	+85	°C

<sup>(2)</sup> All voltage values are with respect to GND. For reliable operation the device must not operate at 7 V for more than t = 1000h continuously.



# **ELECTRICAL CHARACTERISTICS OVER RECOMMENDED OPERATING CONDITIONS (unless otherwise noted)**

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
	FARAMETER		V <sub>DD</sub> = 1.8 V I <sub>OH</sub> = -400 μA	V <sub>DD</sub> – 0.2 V	115	WAY	CIVIT	
		RESET	V <sub>DD</sub> = 1.8 V I <sub>OH</sub> = -400 µA V <sub>DD</sub> = 3.3 V, I <sub>OH</sub> = -2 mA V <sub>DD</sub> = 5 V, I <sub>OH</sub> = -3 mA	V <sub>DD</sub> = 0.2 V				
			$V_{DD} = 1.8 \text{ V},  I_{OH} = -20 \mu\text{A}$	V <sub>DD</sub> – 0.3 V				
Vон	High-level output voltage	RESET	$V_{DD} = 3.3 \text{ V},  I_{OH} = -80 \mu\text{A}$ $V_{DD} = 5 \text{ V},  I_{OH} = -120 \mu\text{A}$	V <sub>DD</sub> – 0.4 V			V	
		CEOUT	$V_{OUT} = 1.8 \text{ V}, I_{OH} = -1 \text{ mA}$	V <sub>OUT</sub> – 0.2 V				
		Enable mode CEIN = VOUT	$V_{OUT} = 3.3 \text{ V}, I_{OH} = -2 \text{ mA}$ $V_{OUT} = 5 \text{ V}, I_{OH} = -5 \text{ mA}$	V <sub>OUT</sub> – 0.3 V				
		CEOUT Disable mode	$V_{OUT} = 3.3 \text{ V}, I_{OH} = -0.5 \text{ mA}$	V <sub>OUT</sub> – 0.4 V				
		RESET	$V_{DD} = 1.8 \text{ V},  I_{OL} = 400 \mu\text{A}$			0.2		
		RESET	$V_{DD} = 3.3 \text{ V},  I_{OL} = 2 \text{ mA}$ $V_{DD} = 5 \text{ V},  I_{OL} = 3 \text{ mA}$			0.4		
		CEOUT	V <sub>OUT</sub> = 1.8 V, I <sub>OL</sub> = 1.0 mA			0.2	V	
VOL	Low-level output voltage	Enable mode CEIN = 0 V	V <sub>OUT</sub> = 3.3 V, I <sub>OL</sub> = 2 mA V <sub>OUT</sub> = 5 V, I <sub>OL</sub> = 5 mA			0.3		
		Power-up reset voltage (see Note 1)	$V_{DD} > 1.1 \text{ V or } V_{BAT} > 1.1 \text{ V},$ $I_{OL} = 20  \mu\text{A}$			0.4	V	
	Normal mode  Battery-backup mode		I <sub>O</sub> = 8.5 mA, V <sub>DD</sub> = 1.8 V, V <sub>BAT</sub> = 0 V	V <sub>DD</sub> – 50 mV				
			$I_O = 125 \text{ mA},$ $V_{DD} = 3.3 \text{ V},  V_{BAT} = 0 \text{ V}$	V <sub>DD</sub> – 150 mV				
VOUT			$I_{O} = 200 \text{ mA},$ $V_{DD} = 5 \text{ V}, \qquad V_{BAT} = 0 \text{ V}$	V <sub>DD</sub> – 200 mV			V	
			I <sub>O</sub> = 0.5 mA, V <sub>BAT</sub> = 1.5 V, V <sub>DD</sub> = 0 V	V <sub>BAT</sub> – 20 mV				
			I <sub>O</sub> = 7.5 mA, V <sub>BAT</sub> = 3.3 V, V <sub>DD</sub> = 0 V	V <sub>BAT</sub> – 113 mV				
R <sub>DS</sub> (on)	V <sub>DD</sub> to V <sub>OUT</sub> on-resistance		V <sub>DD</sub> = 5 V		0.6	1	Ω	
1 103(011)	VBAT to VOUT on-resistant		V <sub>BAT</sub> = 3.3 V		8	15		
VIT	Negative-going input thresh (see Note 2)	old voltage		1.13	1.15	1.17	V	
$V_{hys}$	Hysteresis	Sense	1.1 V < V <sub>IT</sub> < 1.65 V		12		mV	
	-	V <sub>BSW</sub> (see Note 3)	V <sub>DD</sub> = 1.8 V		55		v	
lіН	High-level input current	MR	$\overline{MR} = 0.7 \times V_{DD}, V_{DD} = 5 V$	-33		-76	μΑ	
IIL	Low-level input current		$\overline{MR} = 0 \text{ V}, \qquad V_{DD} = 5 \text{ V}$	-110		-255	•	
lı	Input current	SENSE	V <sub>DD</sub> = 1.15 V	-25		25	nA	
I <sub>DD</sub> V <sub>DD</sub> supply current		$V_{OUT} = V_{DD}$ $V_{OUT} = V_{BAT}$			40 40	μΑ		
I <sub>BAT</sub>	IBAT VBAT supply current		V <sub>OUT</sub> = V <sub>DD</sub>	-0.1		0.1	μΑ	
	CEIN leakage current		Disable mode, V <sub>I</sub> < V <sub>DD</sub>		-	±1	μΑ	
l <sub>lkg</sub>	OLIN ICARAGE CUITCIN		The second secon			1		

<sup>(1)</sup> The lowest voltage at which RESET becomes active.  $t_{\Gamma,(VDD)} \ge 15 \,\mu\text{s/V}$ . (2) To ensure best stability of the threshold voltage, a bypass capacitor (ceramic, 0.1  $\mu$ F) should be placed near to the supply terminals. (3) For  $V_{DD} < 1.6 \,\text{V}$ ,  $V_{OUT}$  switches to  $V_{BAT}$  regardless of  $V_{BAT}$ 



# TIMING REQUIREMENTS AT R<sub>L</sub> = 1 M $\Omega$ , C<sub>L</sub> = 50 PF, T<sub>A</sub> = -40°C TO +85°C

PARAMETER			TEST CONDITIONS			TYP	MAX	UNIT
t <sub>W</sub>	Pulse width	SENSE	$V_{IH} = V_{IT} + 0.2 V,$	$V_{IL} = V_{IT} - 0.2 V$	6			μs

# SWITCHING CHARACTERISTICS AT R $_L$ = 1 M $\Omega,$ $C_L$ = 50 PF, $T_A$ = $-40^{\circ}C$ TO +85°C

	PARAMI	ETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<sup>t</sup> d	Delay time		$\frac{\text{VSENSE} \ge \text{V}_{\text{IT}} + 0.2 \text{ V},}{\text{MR} \ge 0.7 \text{ x V}_{\text{DD}},}$ See timing diagram	60	100	140	ms
<sup>t</sup> PLH	Propagation (delay) time, low-to-high-level output	50% RESET to 50% CEOUT	V <sub>OUT</sub> = V <sub>IT</sub>		15		μs
	Propagation (delay) time, high-to-low-level output	50% CEIN to 50% CEOUT, C <sub>L</sub> = 50 pF only (see Note 5)	V <sub>DD</sub> = 1.8 V		5	15	
			V <sub>DD</sub> = 3.3 V		1.6	5	ns
			V <sub>DD</sub> = 5 V		1	3	
<sup>t</sup> PHL		SENSE to RESET	V <sub>IL</sub> = V <sub>IT</sub> - 0.2 V, V <sub>IH</sub> = V <sub>IT</sub> + 0.2 V		2	5	μs
		MR to RESET	$\begin{split} & \forall \text{SENSE} \geq \forall \text{IT} + 0.2 \ \forall, \\ & \forall \text{IL} = 0.3 \ \text{x} \ \forall \text{DD}, \\ & \forall \text{IH} = 0.7 \ \text{x} \ \forall \text{DD} \end{split}$		0.1	1	μs
(1)	Transition time	V <sub>DD</sub> to V <sub>BAT</sub>	V <sub>IH</sub> = V <sub>BAT</sub> + 0.2 V, V <sub>IL</sub> = V <sub>BAT</sub> - 0.2 V, V <sub>BAT</sub> < V <sub>IT</sub>			3	μs

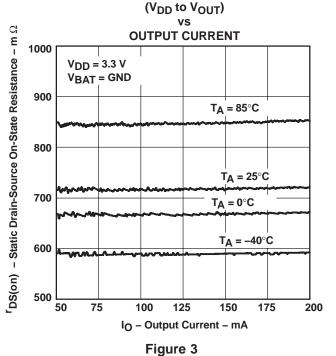
<sup>(1)</sup> Assured by design



#### **Table of Graphs**

			FIGURE
	Static drain-source on-state resistance (V <sub>DD</sub> to V <sub>OUT</sub> )	vs Output current	3
rDS(on)	Static drain-source on-state resistance (VBAT to VOUT)	vs Output current	4
` ,	Static drain-source on-state resistance (CEIN to CEOUT)	vs Input voltage at CEIN	5
IDD	Supply current	vs Supply voltage	6
VIT	Input threshold voltage at RESET	vs Free-air temperature	7
	High-level output voltage at RESET		8, 9
VOH	High-level output voltage at CEOUT	vs High-level output current	10, 11, 12, 13
.,	Low-level output voltage at RESET	vs Low-level output current	14, 15
VOL	Low-level output voltage at CEOUT	vs Low-level output current	16, 17

# STATIC DRAIN-SOURCE ON-STATE RESISTANCE



# STATIC DRAIN-SOURCE ON-STATE RESISTANCE ( $V_{BAT}$ to $V_{OUT}$ )

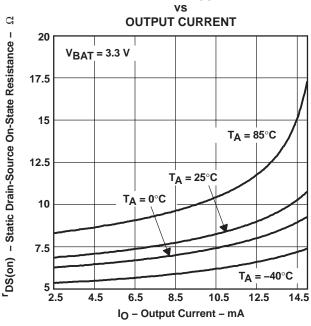


Figure 4



<sup>r</sup>DS(on) - Static Drain Source On-State Resistance

10

5

0

#### TYPICAL CHARACTERISTICS

# STATIC DRAIN-SOURCE ON-STATE RESISTANCE (CEIN to CEOUT) VS INPUT VOLTAGE AT CEIN TA = 85°C TA = 25°C TA = 0°C TA = -40°C

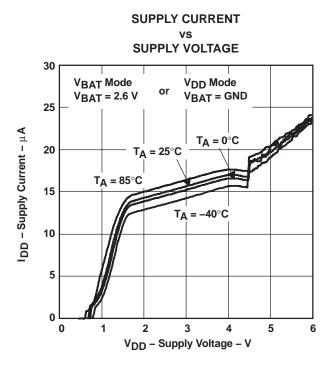


Figure 5

V<sub>I(CEIN)</sub> – Input Voltage at CEIN – V

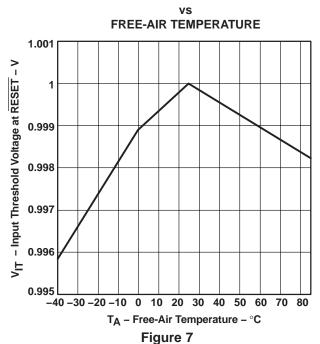
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I<sub>CEOUT</sub> = 5 mA V<sub>DD</sub> = 5 V

Figure 6

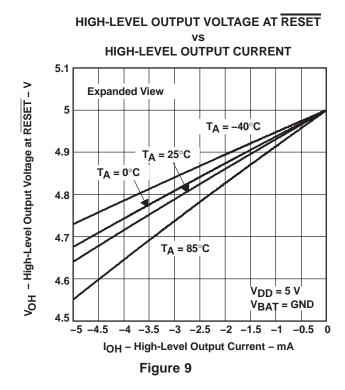
#### INPUT THRESHOLD VOLTAGE AT RESET

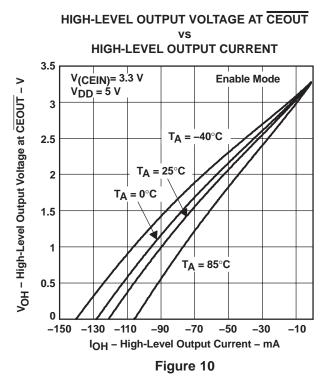
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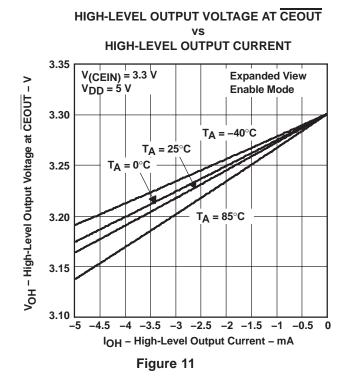




## HIGH-LEVEL OUTPUT VOLTAGE AT RESET HIGH-LEVEL OUTPUT CURRENT 6 $V_{DD} = 5 V$ VOH - High-Level Output Voltage at RESET - V V<sub>BAT</sub> = GND 5 T<sub>A</sub> = -40°C T<sub>A</sub> = 25°C $T_A = 0^{\circ}C$ 2 T<sub>A</sub> = 85°C -20 -15 -10 -5 -35 -25 0 IOH - High-Level Output Current - mA Figure 8

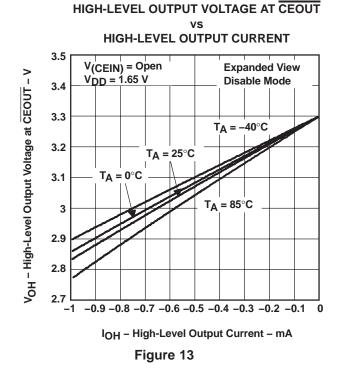




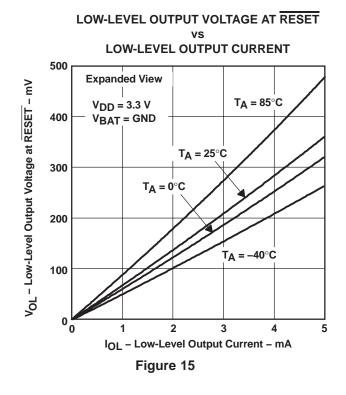




## HIGH-LEVEL OUTPUT VOLTAGE AT CEOUT **HIGH-LEVEL OUTPUT CURRENT** 3.5 V<sub>OH</sub> - High-Level Output Voltage at CEOUT - V 3 $T_A = -40^{\circ}C$ T<sub>A</sub> = 25°C 2.5 $T_A = 0^{\circ}C$ 2 1.5 T<sub>A</sub> = 85°C **Disable Mode** V(CEIN) = Open $V_{DD} = 1.65 \text{ V}$ 0.5 -2.5 -2 -1.5 IOH - High-Level Output Current - mA Figure 12



## LOW-LEVEL OUTPUT VOLTAGE AT RESET LOW-LEVEL OUTPUT CURRENT 3.5 V<sub>OL</sub> - Low-Level Output Voltage at RESET - V $V_{DD} = 3.3 \text{ V}$ $V_{BAT} = GND$ 3 2.5 $T_A = 0^{\circ}C$ 2 T<sub>A</sub> = 25°C 1.5 T<sub>A</sub> = 85°C $T_A = -40^{\circ}C$ 0.5 0 25 0 IOL - Low-Level Output Current - mA Figure 14





## LOW-LEVEL OUTPUT VOLTAGE AT CEOUT **LOW-LEVEL OUTPUT CURRENT** 3.5 **Enable Mode** Vol- Low-Level Output Voltage at CEOUT - V V<sub>(CEIN)</sub> = GND V<sub>DD</sub> = 5 V 2.5 T<sub>A</sub> = 85°C T<sub>A</sub> = 25°C $T_A = 0^{\circ}C$ 1.5 T<sub>A</sub> = -40°C 0.5 40 50 60 70 90 100 IOL - Low-Level Output Current - mA

Figure 16

# LOW-LEVEL OUTPUT VOLTAGE AT CEOUT vs LOW-LEVEL OUTPUT CURRENT

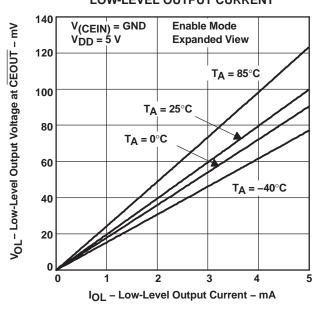


Figure 17



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MENTS

#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPS3613-01DGS	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3613-01DGSG4	ACTIVE	MSOP	DGS	10	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3613-01DGSR	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TPS3613-01DGSRG4	ACTIVE	MSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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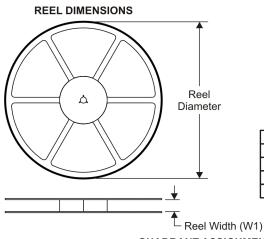
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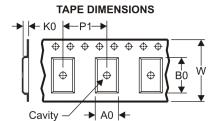


## PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3613-01DGSR	MSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1



PACKAGE MATERIALS INFORMATION

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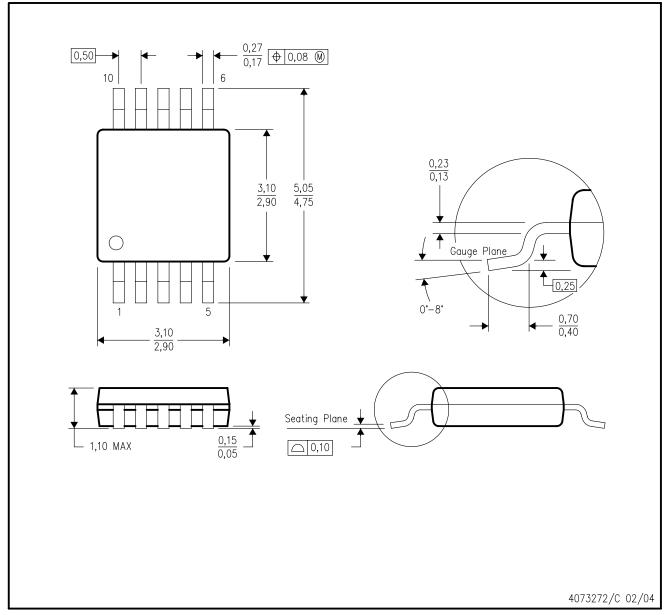


#### \*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TPS3613-01DGSR	MSOP	DGS	10	2500	358.0	335.0	35.0	

# DGS (S-PDSO-G10)

# PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation BA.

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